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N ŏ TO-3PH Ь ٦

N-Channel MOSFET in a TO-3PH Plastic Package.

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ھ Ң$R_{DS(ON)}$ Q_g Ң Ь ɔ

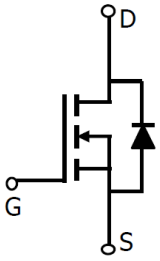
Fast Intrinsic Rectifier,Low $R_{DS(ON)}$ and Q_g,Low Package Inductance

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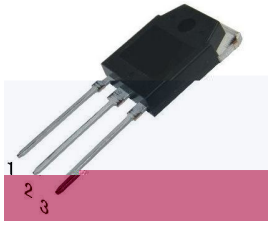
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Switch-Mode and Resonant-Mode Power Supplies,DC-DC Converters,Laser Drivers,AC and DC Motor Drives,Robotics and Servo Controls.

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PIN1 Gate PIN 2 Drain PIN 3 Source

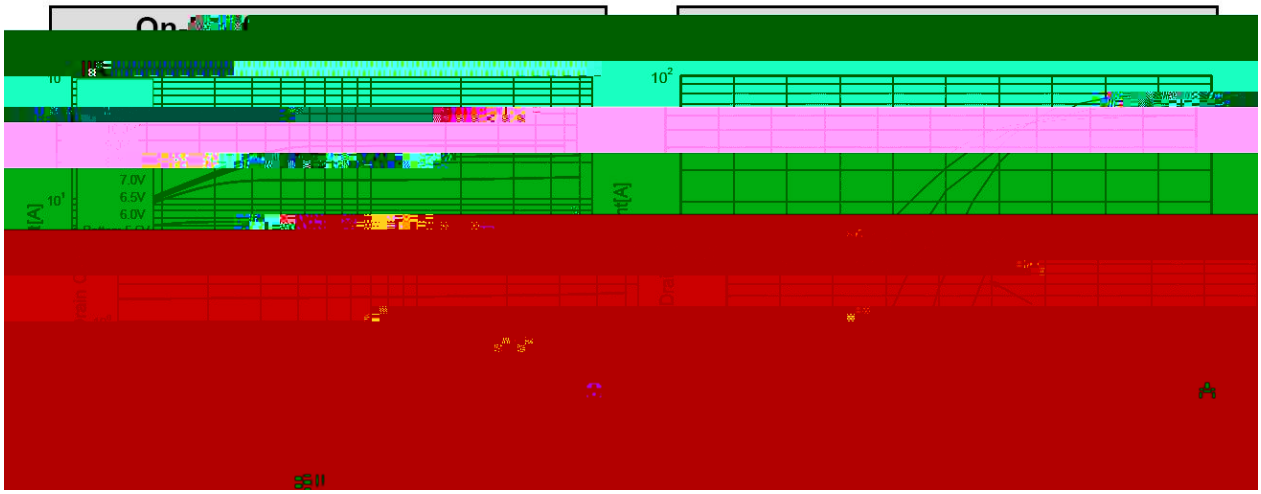
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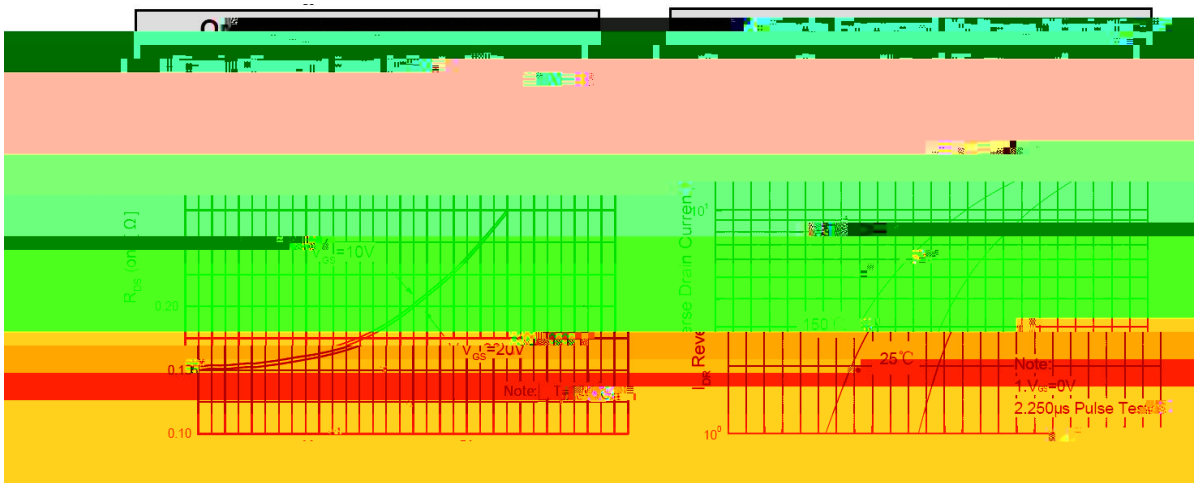
ð ٦ ب See Marking Instructions.

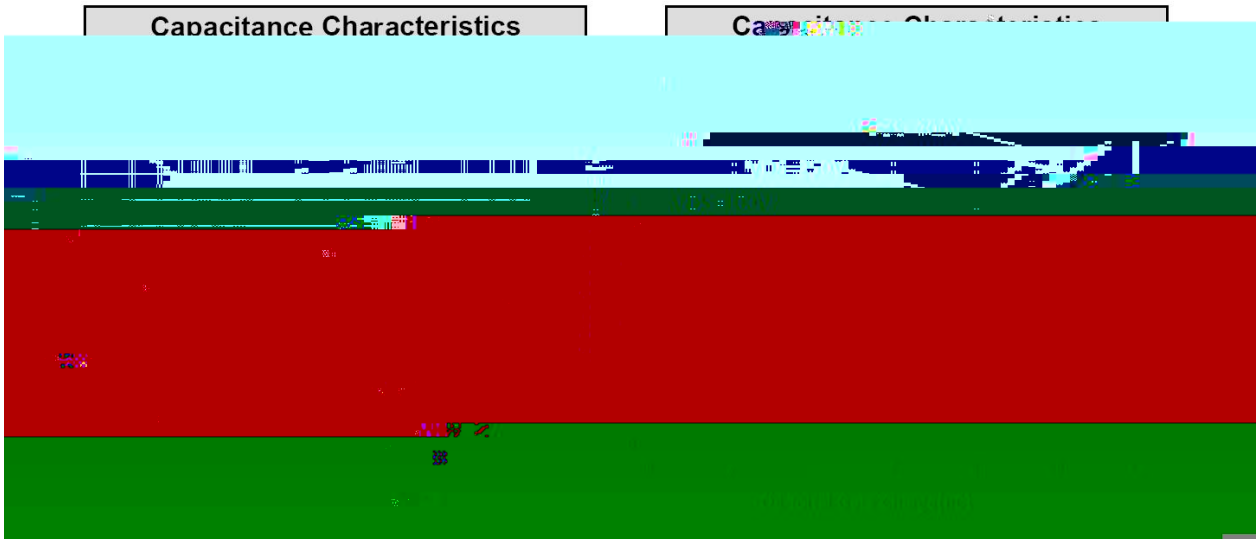
Parameter	Symbol	Rating	Unit
Drain Source Voltage	V_{DSS}	500	V
Gate-Source Voltage	V_{GSS}	±30	V
Drain Continuous- Current(Note 1)	I_D(Tc=25)	26	A

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	500			V
Drain-Source Leakage Current	I_{DSS}	V_{DS}=500V V_{GS}=0V			1	μA

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7.0V
6.5V
6.0V

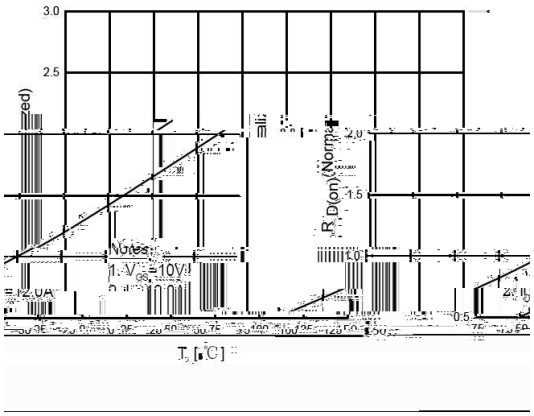

V_GS=10V
V_GS=20V
Note: T_J=25℃
25℃
Note:
1.V_DS=0V
2.250μs Pulse Test


Capacitance Characteristics

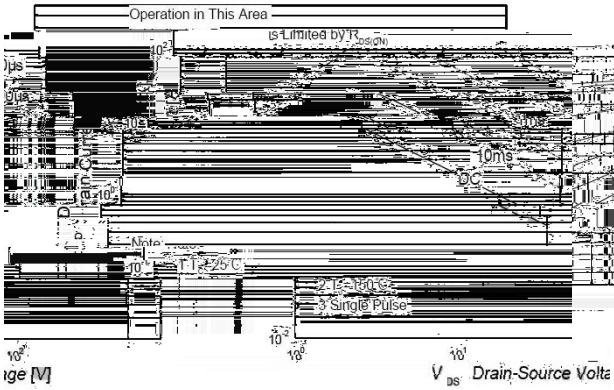
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Breakdown Voltage Variation

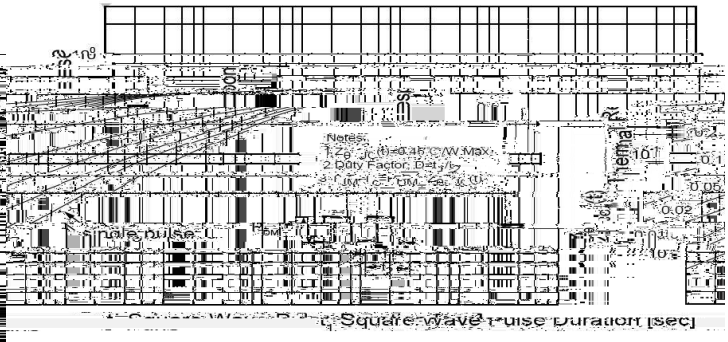
On-Resistance Variation vs. Temperature



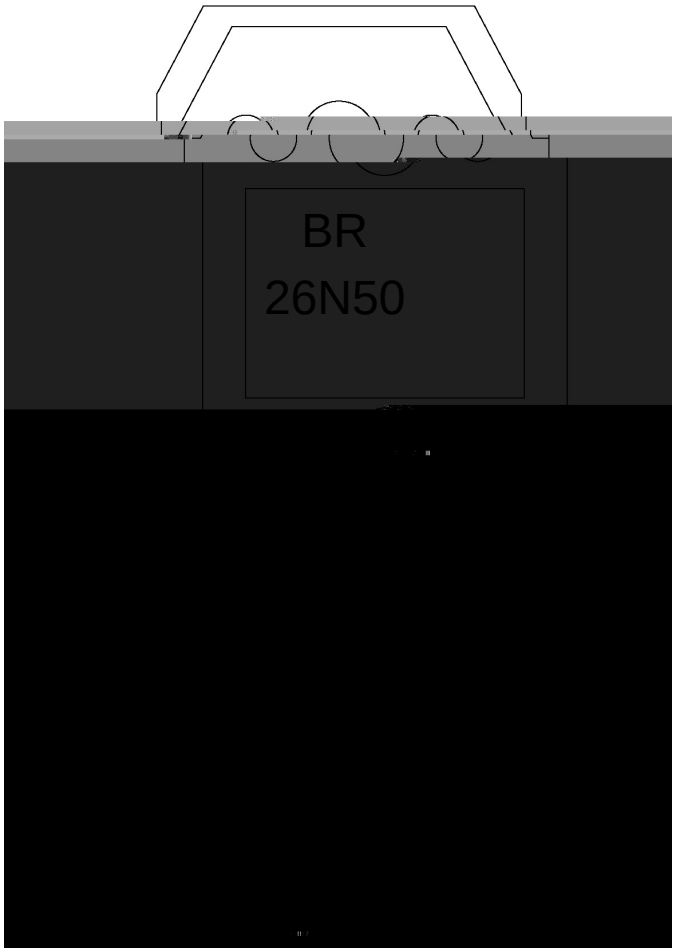
Maximum Safe Operating Area



Transient Thermal Response Curve



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BR: И .

26N50 N .

**** N . ₴ N

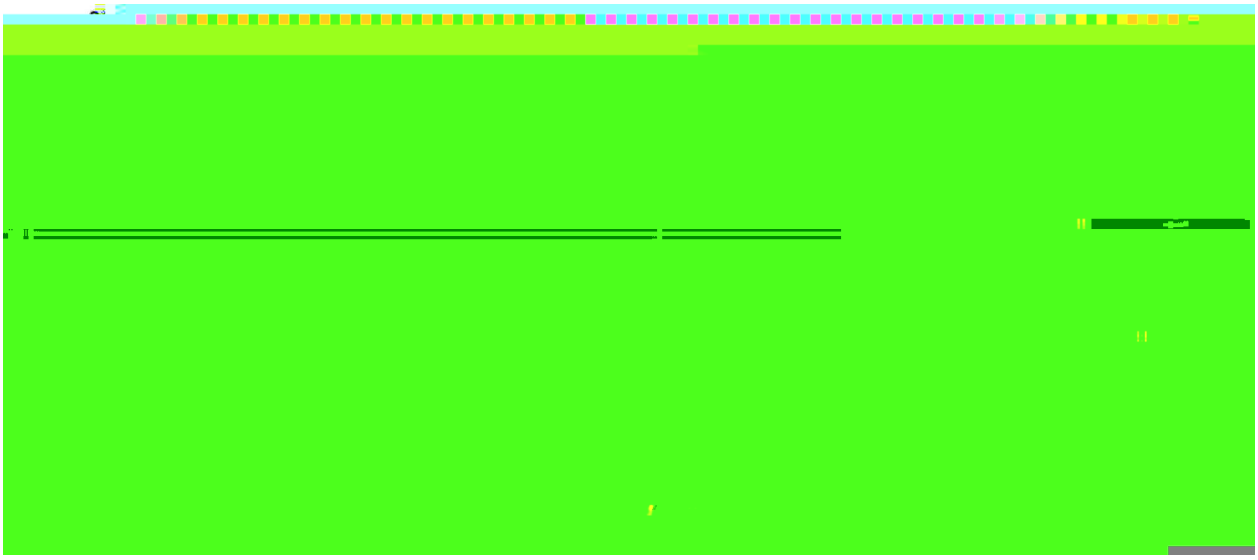
Note:

BR: Company Code.

26N50: Product Type.

****: Lot No. Code, code change with Lot No.

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ب

1 Ĺ 25 150 ژ 60 90sec;

2 255±5 ژ ٨ 5±0.5sec;

3 ٧ ھ 2 10 /sec.

Note:

1.Preheating:25~150 , Time:60~90sec.

2.Peak Temp.:255±5 , Duration:5±0.5sec.

3. Cooling Speed: 2~10 /sec.

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270±5 ژ 10±1 sec. Temp:270±5 Time:10±1 sec

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Package Type	Units					Dimension		(unit mm^3)

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